

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package. This "series ET" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers. It is used in applications where "high junction operating temperature" capability is required.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High junction operating temperature capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

## 3. Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- Motor controls e.g. washing machines and vacuum cleaners
- Refrigeration and air-conditioner compressor controls

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 131 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	10	A
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25 \text{ }^\circ\text{C}$ ; $t_{\text{p}} = 20 \text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	100	A

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G+$ $T_j = 25\text{ °C};$ <a href="#">Fig. 7</a>	0.5	-	10	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G-$ $T_j = 25\text{ °C};$ <a href="#">Fig. 7</a>	0.5	-	10	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2- G-$ $T_j = 25\text{ °C};$ <a href="#">Fig. 7</a>	0.5	-	10	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}; T_j = 150\text{ °C}; (V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	50	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}; T_j = 150\text{ °C}; I_{T(RMS)} = 10\text{ A};$ $dV_{com}/dt = 20\text{ V}/\mu\text{s};$ gate open circuit	5	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

## 6. Ordering information

Table 3. Ordering information

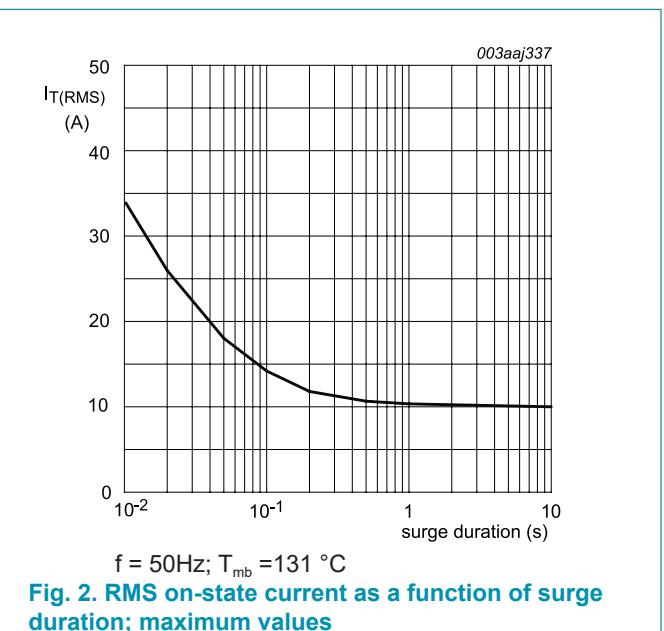
Type number	Package		Version
	Name	Description	
BTA410-800ET	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 131\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	10	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	100	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	110	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ms}$ ; sine-wave pulse	-	50	A <sup>2</sup> s
$dl_T/dt$	rate of rise of on-state current	$I_G = 20\text{ mA}$	-	100	A/ $\mu$ s
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	150	°C



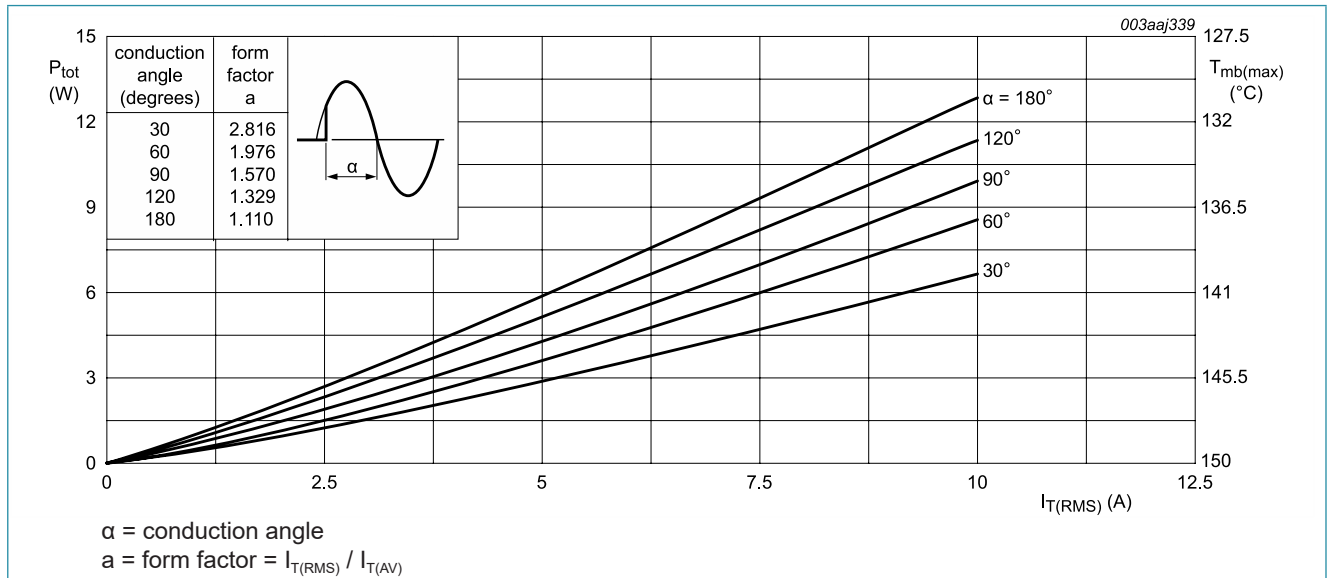


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

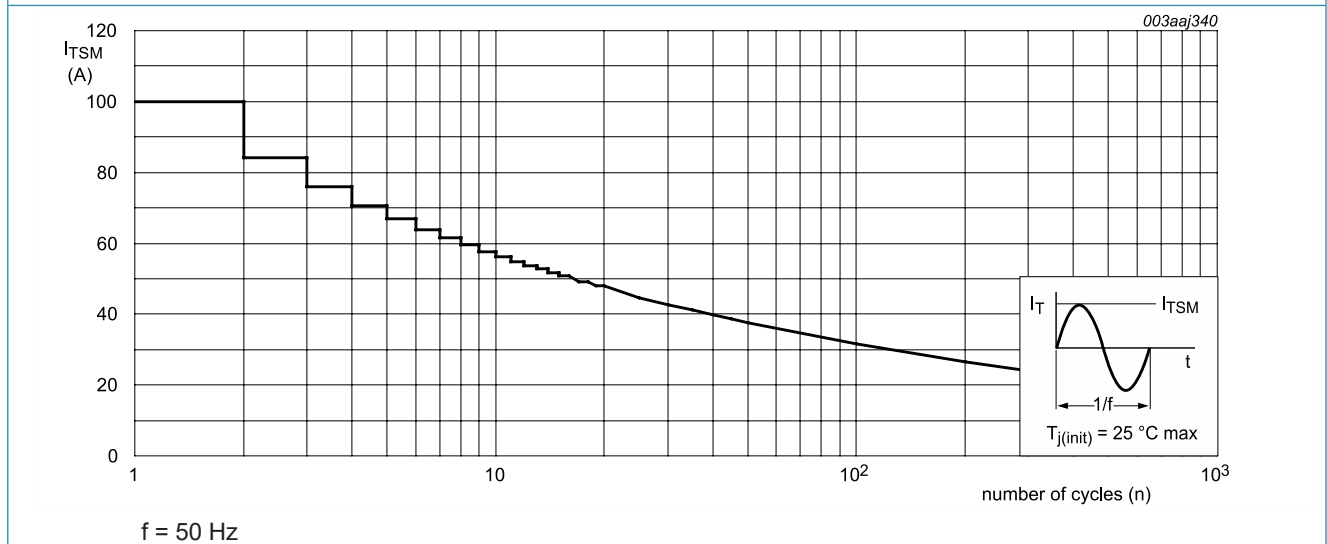


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

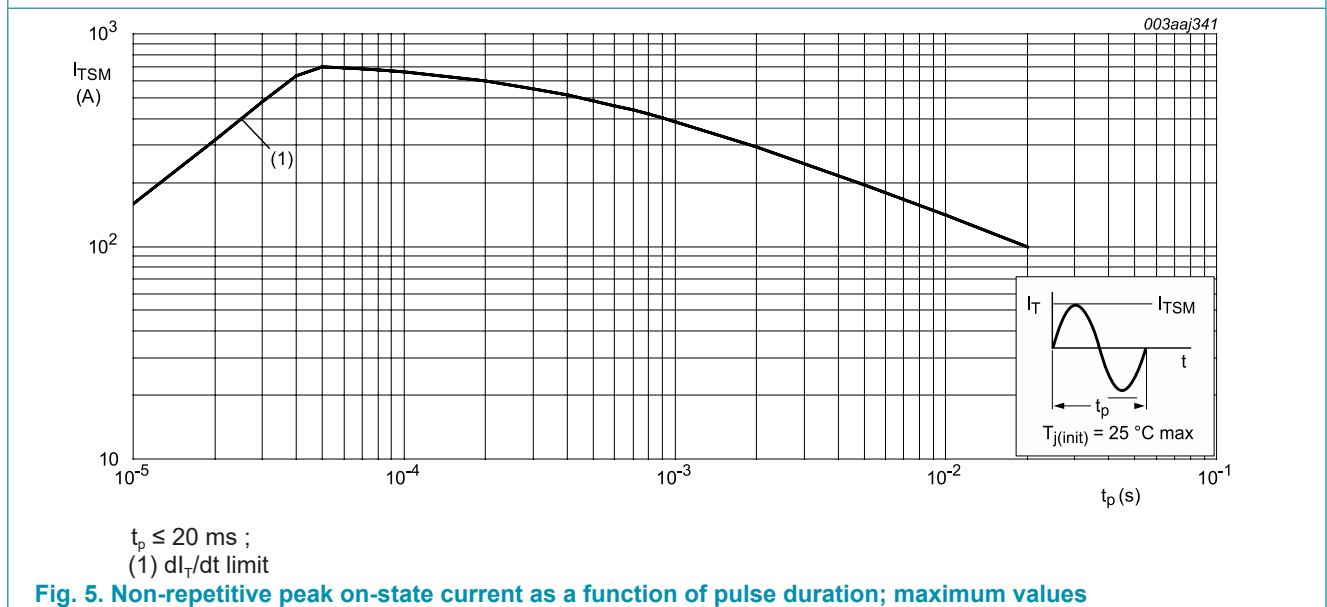


Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

## 8. Thermal characteristics

Table 5. Thermal characteristics

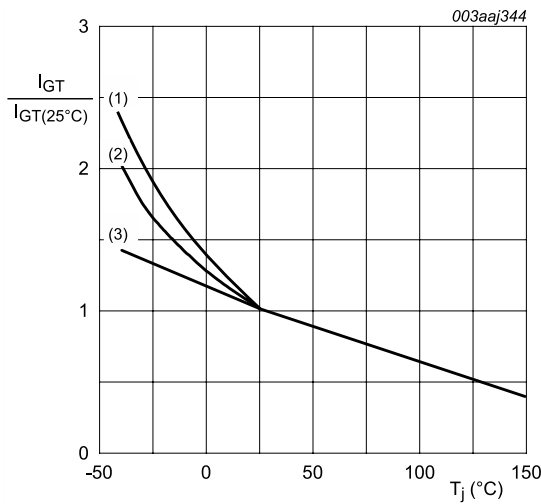
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; <a href="#">Fig. 6</a>	-	-	1.5	K/W
		half cycle; <a href="#">Fig. 6</a>	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G+;$ $T_J = 25\text{ °C};$ <a href="#">Fig. 7</a>	0.5	-	10	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G-;$ $T_J = 25\text{ °C};$ <a href="#">Fig. 7</a>	0.5	-	10	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2- G-;$ $T_J = 25\text{ °C};$ <a href="#">Fig. 7</a>	0.5	-	10	mA
$I_L$	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2+ G+;$ $T_J = 25\text{ °C};$ <a href="#">Fig. 8</a>	-	-	25	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2+ G-;$ $T_J = 25\text{ °C};$ <a href="#">Fig. 8</a>	-	-	30	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2- G-;$ $T_J = 25\text{ °C};$ <a href="#">Fig. 8</a>	-	-	25	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_J = 25\text{ °C};$ <a href="#">Fig. 9</a>	-	-	15	mA
$V_T$	on-state voltage	$I_T = 15\text{ A}; T_J = 25\text{ °C};$ <a href="#">Fig. 10</a>	-	1.3	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; T_J = 25\text{ °C};$ <a href="#">Fig. 11</a>	-	0.7	1	V
		$V_D = 400\text{ V}; T_J = 150\text{ °C};$ <a href="#">Fig. 11</a>	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 800\text{ V}; T_J = 150\text{ °C}$	-	0.4	2	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}; T_J = 150\text{ °C}; (V_{DM} = 67\%$ of $V_{DRM});$ exponential waveform; gate open circuit	50	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}; T_J = 150\text{ °C}; I_{T(RMS)} = 10\text{ A};$ $dV_{com}/dt = 20\text{ V}/\mu\text{s};$ (snubberless condition); gate open circuit	2	-	-	A/ms
		$V_D = 400\text{ V}; T_J = 150\text{ °C}; I_{T(RMS)} = 10\text{ A};$ $dV_{com}/dt = 10\text{ V}/\mu\text{s};$ gate open circuit	3.5	-	-	A/ms
		$V_D = 400\text{ V}; T_J = 150\text{ °C}; I_{T(RMS)} = 10\text{ A};$ $dV_{com}/dt = 1\text{ V}/\mu\text{s};$ gate open circuit	5	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

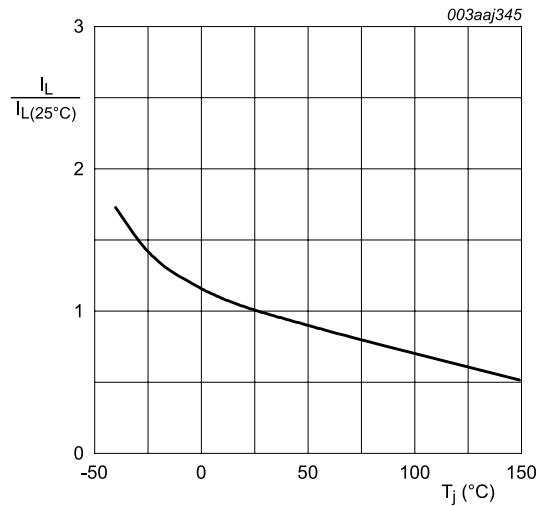


Fig. 8. Normalized latching current as a function of junction temperature

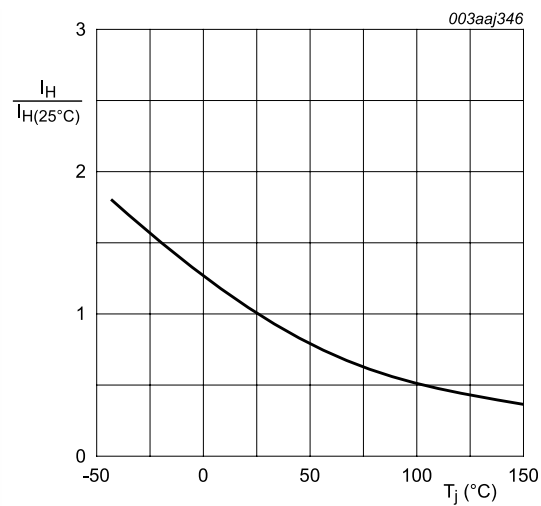
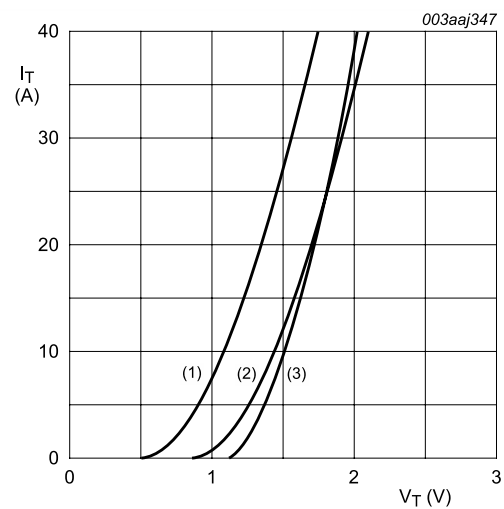


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.142 \text{ V}; R_s = 0.027 \Omega$

- (1)  $T_j = 150^{\circ}\text{C}$ ; typical values
- (2)  $T_j = 150^{\circ}\text{C}$ ; maximum values
- (3)  $T_j = 25^{\circ}\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

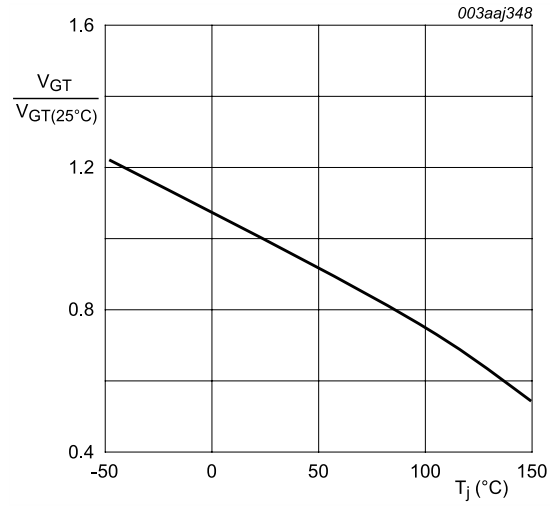


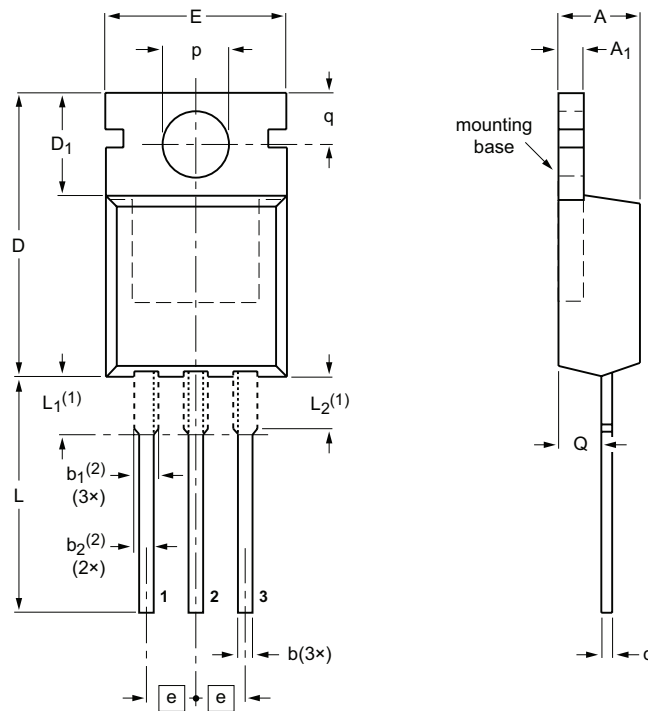
Fig. 11. Normalized gate trigger voltage as a function of junction temperature



### 10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> ( <sup>2</sup> )	b <sub>2</sub> ( <sup>2</sup> )	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> ( <sup>1</sup> )	L <sub>2</sub> ( <sup>1</sup> ) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

**Notes**

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

## 11. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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